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Amendments to the Abstract:

Please amend the abstract as follows:

Abstract

B17

On a substrate made of e.g., sapphire single crystal is formed an Al underlayer having a crystallinity FWHM X-ray rocking curve value of 90 seconds or below in FWHM of X-ray rocking curve. Then, on the AlN underlayer is formed a buffer layer is formed on the AlN underlayer and has having a composition of  $Al_pGa_yIn_{1-p-q}N$  ( $0 \leq p \leq 1$ ,  $0 \leq y \leq q$ ), and A GaN-based semiconductor layer group is formed on the buffer layer, is formed a GaN-based semiconductor layer group.